

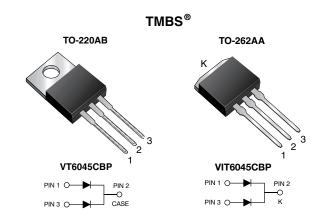
Vishay General Semiconductor

HALOGEN

FREE

# Trench MOS Barrier Schottky Rectifier for PV Solar Cell Bypass Protection

Ultra Low  $V_F = 0.33 \text{ V}$  at  $I_F = 10 \text{ A}$ 



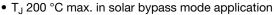
| PRIMARY CHARACTERISTICS                  |                     |  |  |  |
|--|---------------------|--|--|--|
| I <sub>F(AV)</sub>                       | 2 x 30 A            |  |  |  |
| V <sub>RRM</sub>                         | 45 V                |  |  |  |
| I <sub>FSM</sub>                         | 320 A               |  |  |  |
| V <sub>F</sub> at I <sub>F</sub> = 30 A  | 0.47 V              |  |  |  |
| T <sub>OP</sub> max. (AC mode)           | 150 °C              |  |  |  |
| T <sub>J</sub> max. (DC forward current) | 200 °C              |  |  |  |
| Package                                  | TO-220AB, TO-262AA  |  |  |  |
| Diode variation                          | Dual common cathode |  |  |  |

#### **FEATURES**

- Trench MOS Schottky technology
- Low forward voltage drop, low power losses

· High efficiency operation

Solder dip 275 °C max. 10 s, per JESD 22-B106



 Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### TYPICAL APPLICATIONS

For use in solar cell junction box as a bypass diode for protection, using DC forward current without reverse bias.

#### **MECHANICAL DATA**

Case: TO-220AB, TO-262AA

Molding compound meets UL 94 V-0 flammability rating Base P/N-M3 - halogen-free, RoHS-compliant, and

commercial grade

Terminals: Matte tin plated leads, solderable per

J-STD-002 and JESD 22-B102

M3 suffix meets JESD 201 class 1A whisker test

Polarity: As marked

Mounting Torque: 10 in-lbs maximum

| MAXIMUM RATINGS (T <sub>A</sub> = 25 °C unless otherwise noted)                              |            |                                    |             |            |      |  |
|--|------------|------------------------------------|-------------|------------|------|--|
| PARAMETER  |            | SYMBOL                             | VT6045CBP   | VIT6045CBP | UNIT |  |
| Maximum repetitive peak reverse voltage  |            | V <sub>RRM</sub>                   | 45          |            | V    |  |
| Maximum average forward rectified current (fig. 1)   | per device | I (1)                              | 60          |            | А    |  |
|  | per diode  | I <sub>F(AV)</sub> <sup>(1)</sup>  | 30          |            |      |  |
| Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode |            | I <sub>FSM</sub>                   | 320         |            | А    |  |
| Operating junction and storage temperature range (AC mode)                                   |            | T <sub>OP</sub> , T <sub>STG</sub> | -40 to +150 |            | °C   |  |
| Junction temperature in DC forward current without reverse bias, $t \le 1 \text{ h}$         |            | T <sub>J</sub> <sup>(2)</sup>      | ≤ 2         | 200        | °C   |  |

#### **Notes**

- (1) With heatsink
- (2) Meets the requirements of IEC 61215 ed. 2 bypass diode thermal test

# VT6045CBP, VIT6045CBP

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| <b>ELECTRICAL CHARACTERISTICS</b> (T <sub>A</sub> = 25 °C unless otherwise noted) |                            |                         |                               |      |      |      |
|---|----------------------------|-------------------------|-------------------------------|------|------|------|
| PARAMETER   | TEST CONDITIONS            |                         | SYMBOL                        | TYP. | MAX. | UNIT |
| Instantaneous forward voltage per diode   | I <sub>F</sub> = 10 A      | T <sub>A</sub> = 25 °C  | V <sub>F</sub> <sup>(1)</sup> | 0.44 | -    | V    |
|   | I <sub>F</sub> = 15 A      |                         |                               | 0.47 | -    |      |
|   | I <sub>F</sub> = 30 A      |                         |                               | 0.54 | 0.64 |      |
|   | I <sub>F</sub> = 10 A      | T <sub>A</sub> = 125 °C |                               | 0.33 | -    |      |
|   | I <sub>F</sub> = 15 A      |                         |                               | 0.37 | -    |      |
|   | I <sub>F</sub> = 30 A      |                         |                               | 0.47 | 0.56 |      |
| Reverse current per diode   | V - 45 V                   | T <sub>A</sub> = 25 °C  | I <sub>R</sub> <sup>(2)</sup> | -    | 3000 | μΑ   |
|   | $V_R = 45 \text{ V}$ $T_A$ | T <sub>A</sub> = 125 °C |                               | 18   | 50   | mA   |

#### Notes

 $^{(1)}$  Pulse test: 300  $\mu s$  pulse width, 1 % duty cycle

(2) Pulse test: Pulse width ≤ 40 ms

| THERMAL CHARACTERISTICS (T <sub>A</sub> = 25 °C unless otherwise noted) |            |  |            |      |      |
|---|------------|--|------------|------|------|
| PARAMETER   | SYMBOL     | VT6045CBP                              | VIT6045CBP | UNIT |      |
| Typical thermal resistance  | per diode  | В                                      | 1.5        |      | °C/W |
|   | per device | $-$ R <sub><math>\theta</math>JC</sub> | 0.8        |      |      |

| ORDERING INFORMATION (Example) |                  |                 |              |               |               |  |  |
|--------------------------------|------------------|-----------------|--------------|---------------|---------------|--|--|
| PACKAGE                        | PREFERRED P/N    | UNIT WEIGHT (g) | PACKAGE CODE | BASE QUANTITY | DELIVERY MODE |  |  |
| TO-220AB                       | VT6045CBP-M3/4W  | 1.89            | 4W           | 50/tube       | Tube          |  |  |
| TO-262AA                       | VIT6045CBP-M3/4W | 1.45            | 4W           | 50/tube       | Tube          |  |  |



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## **RATINGS AND CHARACTERISTICS CURVES** (T<sub>A</sub> = 25 °C unless otherwise noted)

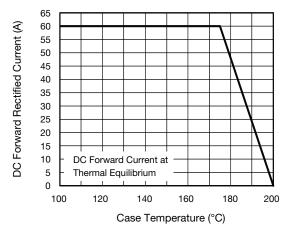


Fig. 1 - Maximum Forward Current Derating Curve

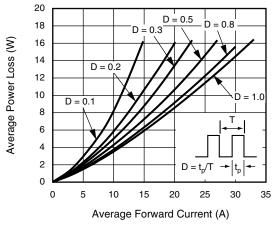


Fig. 2 - Forward Power Loss Characteristics Per Diode

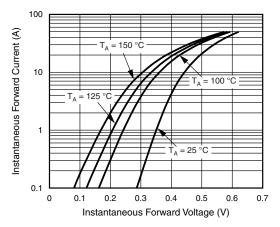


Fig. 3 - Typical Instantaneous Forward Characteristics Per Diode

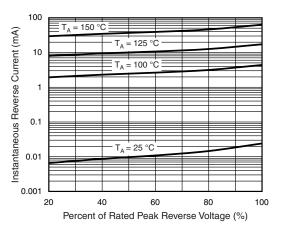


Fig. 4 - Typical Reverse Characteristics Per Diode

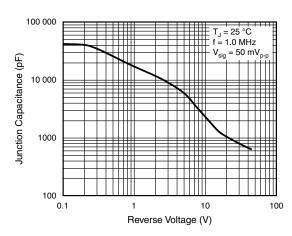


Fig. 5 - Typical Junction Capacitance Per Diode

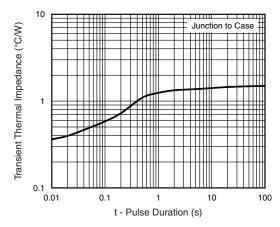
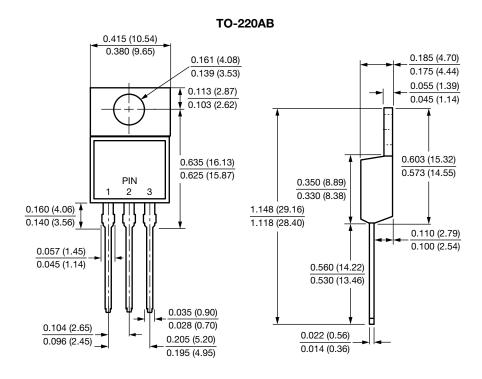


Fig. 6 - Typical Transient Thermal Impedance Per Diode

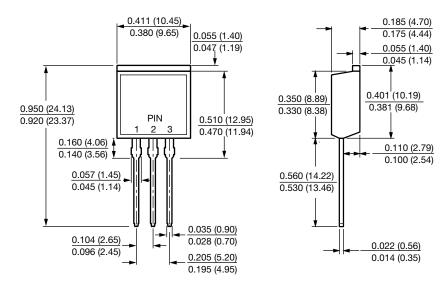


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## PACKAGE OUTLINE DIMENSIONS in inches (millimeters)



### TO-262AA





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